



# MT30N3A

## 主要参数 MAIN CHARACTERISTICS

$I_D$	27A
$V_{DSS}$	30V
$R_{dson-max}$ (@ $V_{gs}=10V$ )	3.4m $\Omega$
$Q_g-typ$	89nC

### 用途

- 电信与工业领域隔离 DC/DC 转换
- 同步整流领域 DC/DC 与 AC/DC 转换

### 产品特性

- 低栅极电荷
- 低  $R_{dson}$
- 开关速度快
- 产品全部经过雪崩测试
- 高抗  $dv/dt$  能力
- RoHS 产品

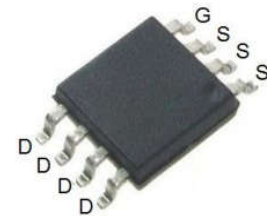
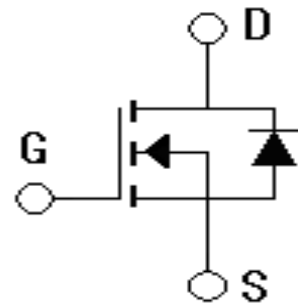
### APPLICATIONS

- Isolated DC/DC Converters in Telecom and Industrial
- Synchronous Rectification in DC/DC and AC/DC Converters

### FEATURES

- Low gate charge
- Low  $R_{dson}$
- Fast switching
- 100% avalanche tested
- Improved  $dv/dt$  capability
- RoHS product

## 封装 Package



SOP-8

## 订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
N/A	N/A	N/A	MT30N3A-L-AR	MT30N3A	SOP-8





## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
		MT30N3A	
最高漏极-源极直流电压 Drain-Source Voltage	$V_{DSS}$	30	V
连续漏极电流 Drain Current -continuous	$I_D$ T=25°C	27*	A
	$I_D$ T=100°C	21*	A
最大脉冲漏极电流 (注1) Drain Current - pulse (note 1)	$I_{DM}$	108*	A
最高栅源电压 Gate-Source Voltage	$V_{GSS}$	±20	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	$E_{AS}$	135	mJ
雪崩电流 (注1) Avalanche Current (note 1)	$I_{AS}$	30	A
耗散功率 Power Dissipation	$P_D$ T <sub>C</sub> =25°C -Derate above 25°C	5	W
		0.04	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300	°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	30	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	1	$\mu A$
		$V_{DS}=30V, V_{GS}=0V,$ $T_C=125^\circ C$	-	-	100	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	1.0	1.7	2.4	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=20A$	-	2.6	3.4	m $\Omega$
		$V_{GS} = 4.5V, I_D=20A$	-	3.6	4.7	m $\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS} = 10V, I_D=20A$ (note 4)	-	30.2	-	S
<b>动态特性 Dynamic Characteristics</b>						
栅电阻 Gate resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, f=1.0MHz$	-	1.17	-	$\Omega$
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	5782	-	pF
输出电容 Output capacitance	$C_{oss}$		-	465	-	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	376	-	pF



**电特性 ELECTRICAL CHARACTERISTICS**

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=20V, I_D=10A, R_G=3.0\Omega,$ (note 3, 4)	-	12	-	ns
上升时间 Turn-On rise time	$t_r$		-	11	-	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	40	-	ns
下降时间 Turn-Off Fall time	$t_f$		-	12	-	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=15V,$ $I_D=30A$ $V_{GS}=10V$ (note 3, 4)	-	89	-	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$		-	9	-	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$		-	16	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	$I_S$	$T_C=25^\circ C$	-	-	27	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$	$T_C=25^\circ C$	-	-	108	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$T_J=25^\circ C, V_{GS}=0V, I_{SD}=30A$	-	-	1.2	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=30A, T_J=25^\circ C$ $dI_F/dt=100A/\mu s$ (note 3)	-	60	-	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr}$		-	120	-	nC

**热特性 THERMAL CHARACTERISTIC**

项 目 Parameter	符 号 Symbol	最大 Max	单位 Unit
		MT30N3A	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	25	$^\circ C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	85	$^\circ C/W$

注释:

1: 脉冲宽度由最高结温限制

2:  $I_{AS}=30A, V_{DD}=50V, V_{GS}=10V, L=0.1mH, R_G=25\Omega$ , 起始结温  $T_J=25^\circ C$ 3: 脉冲测试: 脉冲宽度 $\leq 300\mu s$ , 占空比 $\leq 2\%$ 

4: 基本与工作温度无关

Notes:

1: Pulse width limited by maximum junction temperature

2:  $I_{AS}=30A, V_{DD}=50V, V_{GS}=10V, L=0.1mH, R_G=25\Omega$ , Starting  $T_J=25^\circ C$ 3: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ 

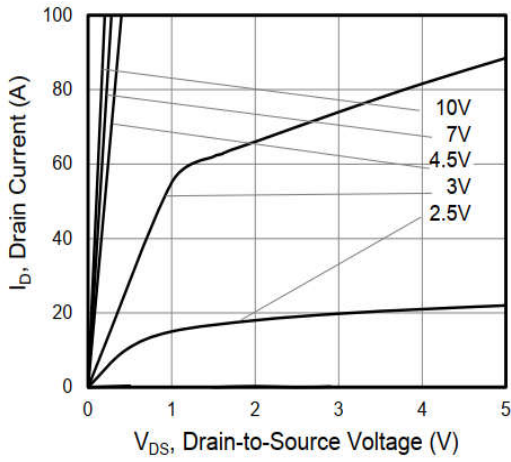
4: Essentially independent of operating temperature



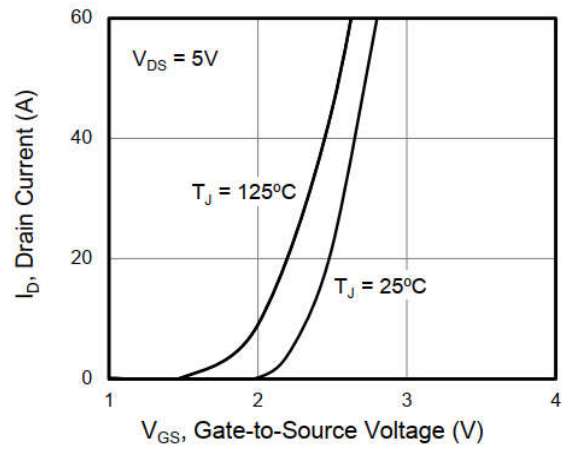


特征曲线 ELECTRICAL CHARACTERISTICS (curves),  $T_J = 25^\circ\text{C}$

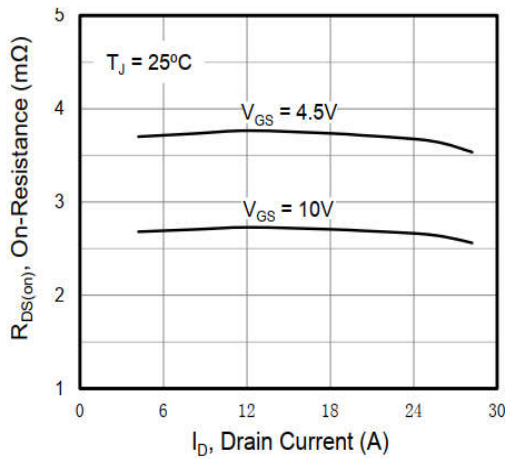
On-Region Characteristics



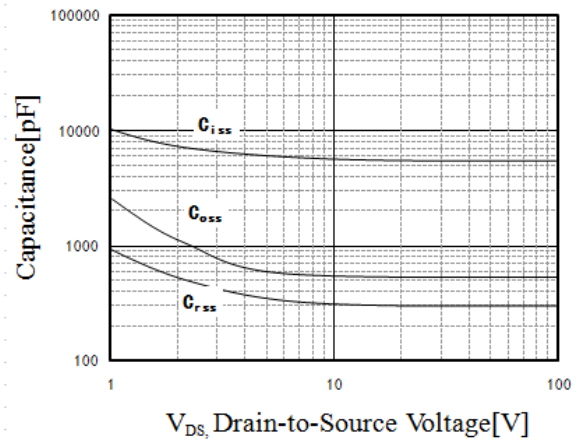
Transfer Characteristics



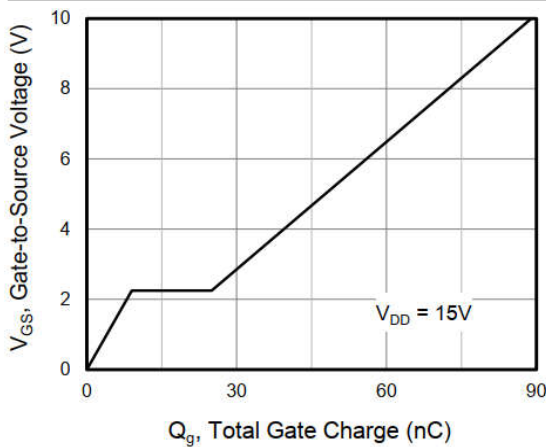
On-Resistance Variation vs. Drain Current and Gate Voltage



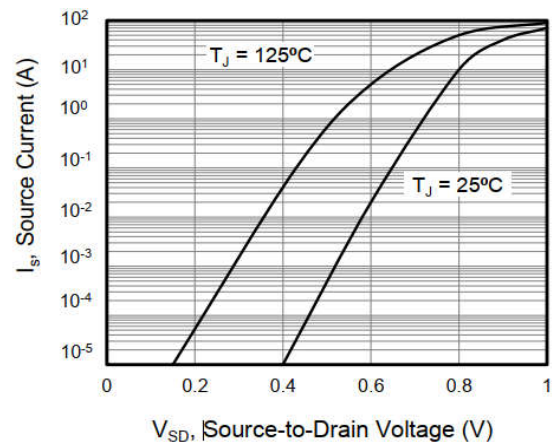
Capacitance Characteristics



Gate Charge Characteristics

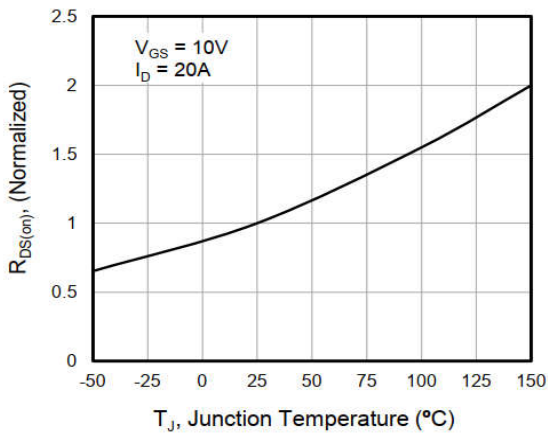


Body Diode Forward Voltage Variation vs. Source Current and Temperature

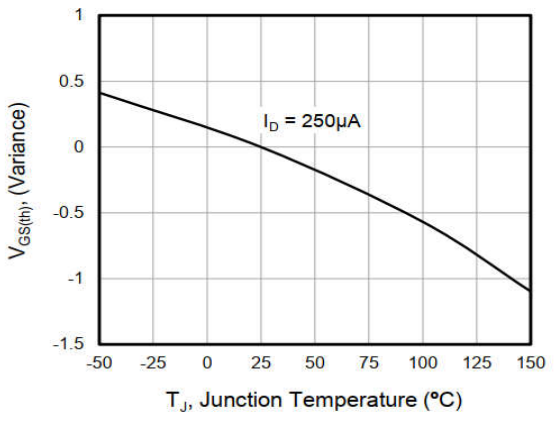




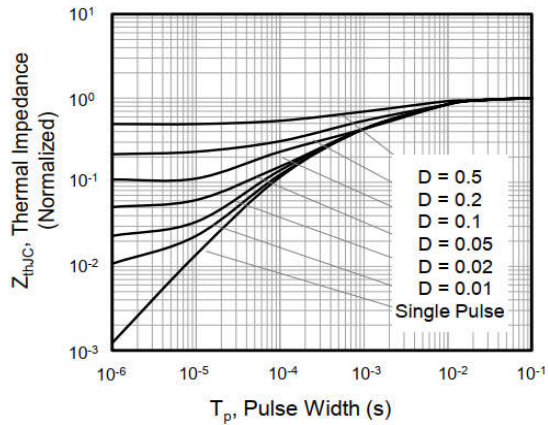
### On-Resistance Variation vs. Junction Temperature



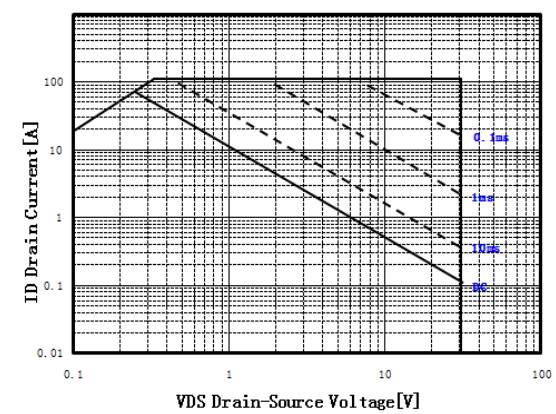
### Threshold Voltage Variation vs. Junction Temperature



### Transient Thermal Impedance



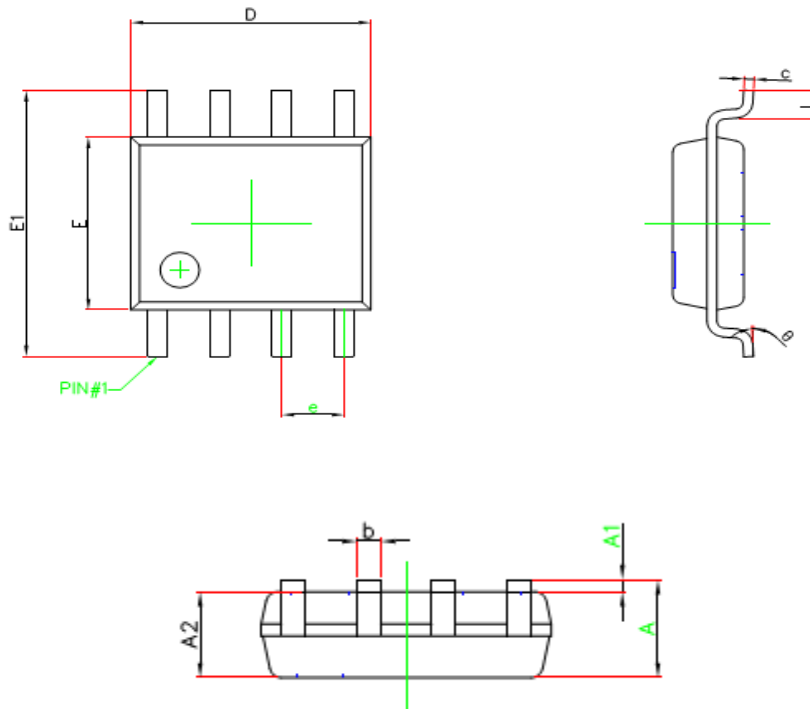
### Maximum Safe Operation





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单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	1.350	1.750
A1	0.100	0.250
A2	1.350	1.550
b	0.330	0.510
c	0.170	0.250
D	4.800	5.200
E	3.800	4.200
E1	5.800	6.200
e	1.27 (TYP)	
L	0.400	1.270
θ	0°	8°



**注意事项**

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